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B/O Form PTO-1449	Atty. Docket Number <b>CHAN3228/EM</b>	Serial Number <b>10/699.839</b>
U.S. Department of Commerce Patent and Trademark Office	Applicant <b>Edward Y. CHANG et. al.</b>	
Information Disclosure Statement by Applicant	Filing Date <b>November 4, 2003</b>	Group <b>Unassigned</b>

U.S. Patent Documents

Examiner Initial	Document Number	Date	Patentee/Applicant	Class	Subclass	Filing Date if Appropriate
MAH	5,959,308	09/28/1999	Shichijo et. al.			01/29/1993
MAH	5,879,962	03/09/1999	DePuydt et. al.			12/13/1995
MAH	5,473,174	12/05/1995	Ohsawa			11/28/1994
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Foreign Patent Documents

Examiner Initial	Document Number	Publication Date	Country/Agency	Class	Subclass	Translation	
						Yes	No

Other Documents (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)

MAH	J. A. Carlin et. al., <i>Impact of GaAs buffer thickness on electronic quality of GaAs grown on graded Ge/GeSi/Si substrates</i> , April 2000, American Institute of Physics, Applied Physics Letters, Vol. 76, No. 14, pp. 1884-1886.
MAH	R. D. Bringans et. al., <i>Use of ZnSe as an interlayer for GaAs growth on Si</i> , July 1992, American Institute of Physics, Applied Physics Letters, Vol. 61, No. 2, pp. 195-197.
MAH	J. Arokiaaraj et. al., <i>High-quality GaAs on Si substrate by the epitaxial lift-off technique using SeS<sub>2</sub></i> , December 1999, American Institute of Physics, Applied Physics Letters, Vol. 75, No. 24, pp. 3826-3828.
MAH	C. Kadow et. al., <i>Subpicosecond carrier dynamics in low-temperature grown GaAs on Si substrates</i> , October 1999, American Institute of Physics, Applied Physics Letters, Vol. 75, No. 17, pp. 2575-2577.
MAH	Y. R. Xing et. al., <i>Growth of high quality gallium arsenide on HF-etched silicon (001) by chemical beam epitaxy</i> , April 1993, American Institute of Physics, Applied Physics Letters, Vol. 62, No. 14, pp. 1653-1655.
MAH	Michael Y. Frankel et. al., <i>Integration of low-temperature GaAs on Si substrates</i> , January 1993, American Institute of Physics, Applied Physics Letters, Vol. 62, No. 3, pp. 255-257.

Examiner <i>Markuson</i>	Date Considered <i>06/14/05</i>
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EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; Draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



B/D Form PTO-1449  U.S. Department of Commerce Patent and Trademark Office  Information Disclosure Statement by Applicant	Atty.CKET Number <b>CHAN3228/REF</b>	Serial Number <b>10/699,839</b>
	Applicant <b>Edward Y. CHANG et al.</b>	
	Filing Date <b>November 4, 2003</b>	Group <b>2818</b>

## U.S. Patent Documents

Examiner Initial	Document Number	Date	Patentee/Applicant	Class	Subclass	Filing Date if Appropriate

## Foreign Patent Documents

Examiner Initial	Document Number	Publication Date	Country/Agency	Class	Subclass	Translation	
						Yes	No
UK	092120501	28/07/2003	Taiwan (English Abstract)				
UK	092120502	28/07/2003	Taiwan (English Abstract)				

## Other Documents (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)


Examiner <i>Michaelson</i>	Date Considered <i>06/14/05</i>
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